MA27D30

Silicon epitaxial planar type

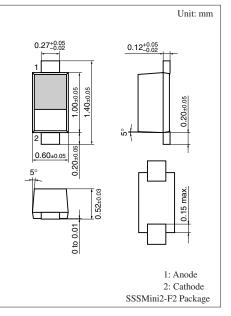
For super high speed switching

Features

- Small reverse current: $I_R < 2 \mu A$ (at $V_R = 30 V$)
- Optimum for high frequency rectification because of its short reverse recovery time t_{rr}.

$\begin{tabular}{ c c c c c c } \hline Parameter & Symbol & Rating & Unit \\ \hline Reverse voltage & V_R & 30 & V \\ \hline Repetitive peak reverse voltage & V_{RRM} & 30 & V \\ \hline Forward current (Average) & I_{F(AV)} & 100 & mA \\ \hline Peak forward current & I_{FM} & 200 & mA \\ \hline Non-repetitive peak forward & I_{FSM} & 1 & A \\ \hline surge current * & & & & \\ \hline \end{tabular}$	Absolute Maximum Hatings $T_a = 25$ C						
Repetitive peak reverse voltage V_{RRM} 30 V Forward current (Average) $I_{F(AV)}$ 100mAPeak forward current I_{FM} 200mANon-repetitive peak forward I_{FSM} 1A	Parameter	Symbol	Rating	Unit			
$\begin{tabular}{ c c c c c c c c c c c c c c c c c c c$	Reverse voltage	V _R	30	V			
Peak forward current I_{FM} 200mANon-repetitive peak forward I_{FSM} 1A	Repetitive peak reverse voltage	V _{RRM}	30	V			
Non-repetitive peak forward I_{FSM} 1A	Forward current (Average)	I _{F(AV)}	100	mA			
	Peak forward current	I_{FM}	200	mA			
surge current *	* *	I _{FSM}	1	А			
	surge current *						
Junction temperature T _j 125 °C	Junction temperature	Tj	125	°C			
Storage temperature T_{stg} -55 to +125 °C	Storage temperature	T _{stg}	-55 to +125	°C			

Absolute Maximum Ratings $T_a = 25^{\circ}C$



Marking Symbol: 8N

Note) * : The peak-to-peak value in one cycle of 50 Hz sine wave (non-repetitive)

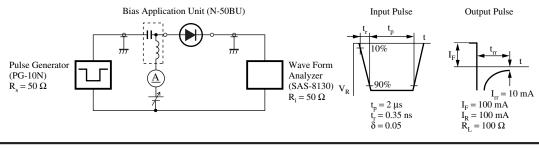
Electrical Characteristics $T_a = 25^{\circ}C \pm 3^{\circ}C$

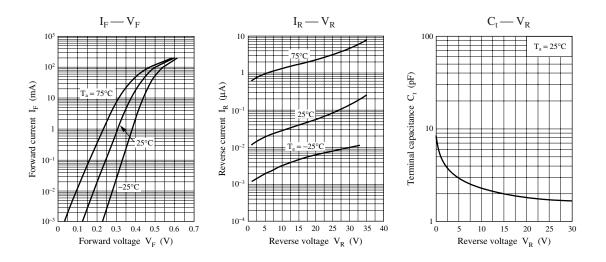
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Forward voltage	V _{F1}	$I_F = 10 \text{ mA}$		0.38	0.44	V
	V _{F2}	I _F = 100 mA		0.51	0.58	V
Reverse current	I _{R1}	V _R = 10 V			0.3	μΑ
	I _{R2}	$V_R = 30 V$			2	μΑ
Terminal capacitance	Ct	$V_R = 0 V, f = 1 MHz$		9		pF
Reverse recovery time *	t _{rr}	$I_F = I_R = 100 \text{ mA}$		1		ns
		$I_{rr} = 10 \text{ mA}, R_L = 100 \Omega$				

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7031 measuring methods for diodes.

2. This product is sensitive to electric shock (static electricity, etc.). Due attention must be paid on the charge of a human body and the leakage of current from the operating equipment.

- 3. Absolute frequency of input and output is 250 MHz
- 4. *: t_{rr} measurement circuit





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